

GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER-III (New) EXAMINATION – WINTER 2018

Subject Code:2132003

Date:01/12/2018

Subject Name:Design Concepts in Basic Electronics

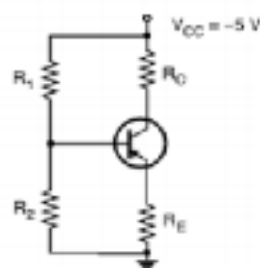
Time:10:30 AM TO 01:00 PM

Total Marks: 70

Instructions:

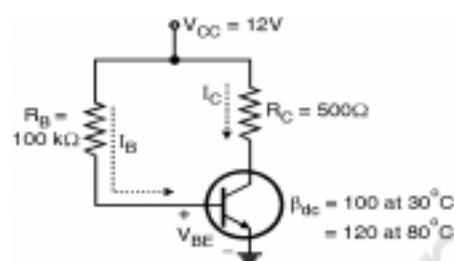
1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

- Q.1**
- (a) Explain in detail different types of breakdown in diode. **03**
 - (b) What are the factors affecting the stability of Q point? **04**
 - (c) Explain DC load line and Q-point for any transistor configuration. Also state the necessity of biasing and list biasing methods for transistor **07**
- Q.2**
- (a) What is energy band diagram? **03**
 - (b) Explain with circuit diagram positive clamper and negative clamper. **04**
 - (c) Explain the input output characteristics of n-p-n transistor in CE configuration. Also indicate different regions. **07**
- OR**
- (c) A circuit receive a 4-bit excess-3 code. Design a minimal circuit to detect a decimal number 0,1,4,6,7 and 8 **07**
- Q.3**
- (a) Draw and explain internal construction of encoder. **03**
 - (b) Explain in detail bidirectional shift register with parallel load **04**
 - (c) Design a combinational logic to convert given BCD to seven segment display LED. **07**
- OR**
- Q.3**
- (a) Write the points of difference between combinational and sequential logic. **03**
 - (b) Draw the circuit diagram of D-type positive edge triggered flip flop **04**
 - (c) Write a note on collector to base bias. **07**
- Q.4**
- (a) What is ripple counter? **03**
 - (b) Implement 32x1 Multiplexer using four 8x1 Multiplexer and one 4x1 Multiplexer **04**
 - (c) A p-n-p germanium transistor is used in the self biasing arrangement with $V_{CC} = 5V$, $R_1 = 27k$, $R_2 = 3k$, $R_E = 270 \Omega$, $R_C = 2k$ and $\beta = 50$. Find V_{CEQ} and I_{CQ} . **07**



OR

- Q.4**
- (a) Explain with example working of transistor as switch. 03
 - (b) Design 3- bit up synchronous counter. 04
 - (c) The fixed bias circuit of Fig. uses a silicon transistor. The component values are $R_C = 500\ \Omega$ and $R_B = 100\ k\Omega$. β_{dc} of the transistor is 100 at 30°C and increases to 120 at a temperature of 80°C . Determine the percent change in the Q point values over this temperature range. Assume that V_{BE} and I_{CBO} remain constant. 07



- Q.5**
- (a) Explain the requirement of complement in digital logic. 03
 - (b) Implement the following function with help of 8x1 Multiplexer.
 $F(A,B,C,D) = \sum (0,1,3,4,8,9,15)$ 04
 - (c) Explain with neat diagram Voltage divider bias 07
- OR
- Q.5**
- (a) Why we require master slave or edge triggered flip flop 03
 - (b) Write a short note on surface mount transistors. 04
 - (c) Compare in detail RTL, DTL, TTL, ECL and CMOS. 07
